Abstract of the Disclosure

A method of manufacturing a semiconductor device on a silicon-on-insulator wafer including a silicon active layer having at least two die pads formed thereon, the at least two die pads separated by at least one scribe lane, including the steps of forming at least one cavity through the silicon active layer in the at least one scribe lane; forming at least one gettering plug in each said cavity, each said gettering plug comprising doped fill material containing a plurality of gettering sites; and subjecting the wafer to conditions to getter at least one impurity into the plurality of gettering sites. A silicon-on-insulator semiconductor wafer including a silicon active layer; a plurality of die pads formed in the silicon active layer; at least one scribe lane between and separating adjacent die pads; and at least one gettering plug in the at least one scribe lane, wherein the at least one gettering plug extends through the silicon active layer and the gettering plug comprises a doped fill material having a plurality of gettering sites.